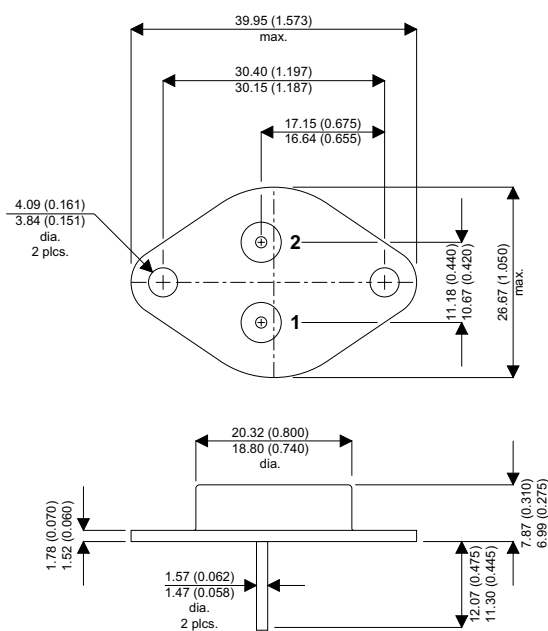


**MECHANICAL DATA**

Dimensions in mm



**TO3B**

Pin 1 – Base      Pin 2 – Emitter      Case – Collector

**NPN MULTI-EPITAXIAL TRANSISTOR**

**FEATURES**

- LOW  $V_{CE(SAT)}$
- FAST SWITCHING
- SINGLE CHIP CONSTRUCTION
- HIGH SWITCHING CURRENTS
- HIGH RELIABILITY
- MILITARY OPTIONS AVAILABLE

**APPLICATIONS**

- SWITCHING REGULATORS
- MOTOR DRIVE CONTROL
- HIGH POWER CONVERTORS

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{CEX}$	Collector – Emitter Voltage ( $V_{BE} = -1.5V$ )	500V
$V_{CEO}$	Collector – Emitter Voltage ( $I_B = 0$ )	275V
$V_{EBO}$	Emitter – Base Voltage	10V
$I_C$	Collector Current	50A
$I_{C(PK)}$	Peak Collector Current	70A
$P_{tot}$	Total Dissipation at $T_{case} = 25^{\circ}C$	300W
$T_{stg}$	Storage Temperature	-55 to 200°C
$T_J$	Maximum Operating Junction Temperature	200°C
$R_{th}$	Thermal Resistance (junction-case)	Max. 0.58°C/W

**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CEX}$ Collector Cut-Off Current	$V_{BE} = 1.5V$ $V_{CEX} = 500V$			0.1	mA
	$T_C = 150^{\circ}C$			5	
$I_{EBO}$ Emitter Cut-Off Current	$V_{BE} = 8V$			0.1	mA
$V_{CE(sat)}$ Collector – Emitter Saturation Voltage	$I_C = 20A$ $I_B = 2A$		0.4	0.6	V
	$I_C = 40A$ $I_B = 5.5A$		0.8	1.0	
$V_{BE(sat)}$ Base – Emitter Saturation Voltage	$I_C = 20A$ $I_B = 2A$		1.0	1.2	V
	$I_C = 40A$ $I_B = 4A$		1.1	1.3	
$h_{FE}$ DC Current Gain	$I_C = 16A$ $V_{CE} = 4V$	20	35		—
	$I_C = 35A$ $V_{CE} = 4V$	10	20		

**SWITCHING CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$t_s$ Storage Time	$I_C = 20A$ $V_{CC} = 200V$			1.8	$\mu s$
$t_f$ Fall Time	$I_{B1} = -I_{B2} = 10A$			0.35	